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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No. .... 10/041,896  
Filing Date ..... January 7, 2002  
Inventorship ..... Brenda D. Kraus et al.  
Assignee ..... Micron Technology, Inc.  
Group Art Unit ..... 2813  
Examiner ..... Yennhu B. Huynh  
Attorney's Docket No. .... MI22-1859  
Customer No. .... 021567  
Title: DRAM Circuitry Having Storage Capacitors Which Include Capacitor  
Dielectric Regions Comprising Aluminum Nitride

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

References - See Attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. Copies of the cited art are attached hereto. No admission is made regarding whether all the submitted references are prior art.

This Supplemental Information Disclosure Statement is being filed before the mailing of a first office action after the filing of a request for continued examination. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 11-20-03By: [Signature]  
Mark S. Matkin  
Reg. No. 32,268

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